捷多邦,专业PCB打样工厂,24小时加急出货



RJK6014DPK

Silicon N Channel MOS FET High Speed Power Switching

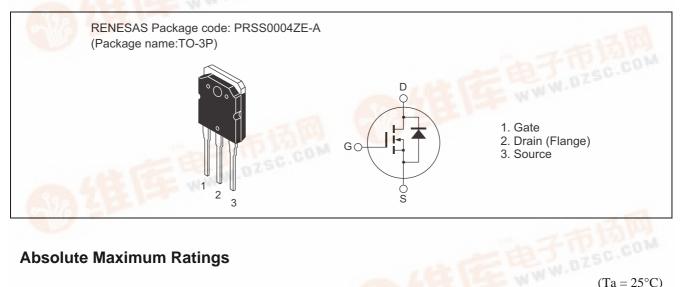
> REJ03G1517-0200 Rev.2.00 Jun 04, 2007

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Features

- Low on-resistance
- Low leakage current
- High speed switching •

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$	
Item	Symbol	Ratings	Unit	
Drain to source voltage	V _{DSS}	600	V	
Gate to source voltage	V _{GSS}	±30	V	
Drain current	Ι _D	16	А	
Drain peak current	Note1 D (pulse)	32	А	
Body-drain diode reverse drain current	I _{DR}	16	A	
Body-drain diode reverse drain peak current	Note1 DR (pulse)	32	А	
Avalanche current	I _{AP} ^{Note3}	5	A col	
Avalanche energy	E _{AR} ^{Note3}	1.3	mJ	
Channel dissipation	Pch Note2	150	W	
Channel to case thermal impedance	θch-c	0.833	°C/W	
Channel temperature	Tch	150	۵°	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. $PW \le 10 \mu s$, duty cycle $\le 1\%$

- 2. Value at $Tc = 25^{\circ}C$
- 3. STch = 25°C, Tch ≤ 150°C



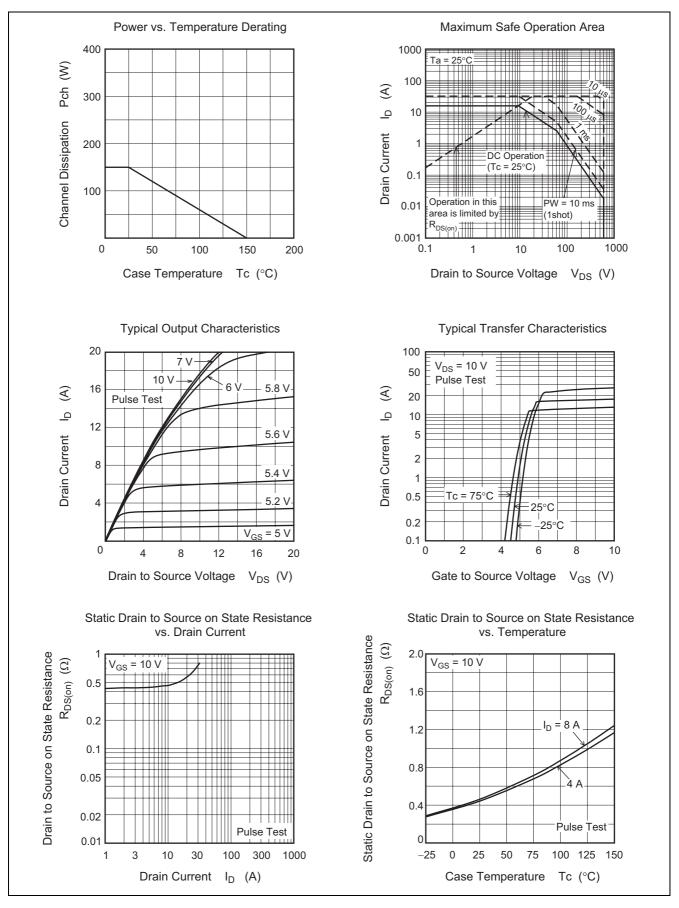
Electrical Characteristics

						(Ta = 25°C)
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	600	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	—	—	1	μΑ	$V_{DS} = 600 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I _{GSS}	—	—	±0.1	μΑ	$V_{GS}=\pm 30~V,~V_{DS}=0$
Gate to source cutoff voltage	V _{GS(off)}	3.0	—	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	_	0.475	0.575	Ω	$I_D = 8 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance						
Input capacitance	Ciss	_	1800	_	pF	V _{DS} = 25 V
Output capacitance	Coss	—	170	_	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	—	20	-	pF	
Turn-on delay time	t _{d(on)}	_	36		ns	I _D = 8 A
Rise time	tr	_	29	_	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	_	93	_	ns	$R_{L} = 37.5 \Omega$ $Rg = 10 \Omega$
Fall time	t _f		20	_	ns	
Total gate charge	Qg		45	_	nC	V _{DD} = 480 V
Gate to source charge	Qgs		9		nC	V _{GS} = 10 V I _D = 16 A
Gate to drain charge	Qgd	_	20	_	nC	
Body-drain diode forward voltage	V_{DF}	_	0.91	1.50	V	$I_F = 16 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t _{rr}	—	390	—	ns	$I_F = 16 \text{ A}, V_{GS} = 0$
						$di_F/dt = 100 \text{ A}/\mu \text{s}$

Notes: 4. Pulse test

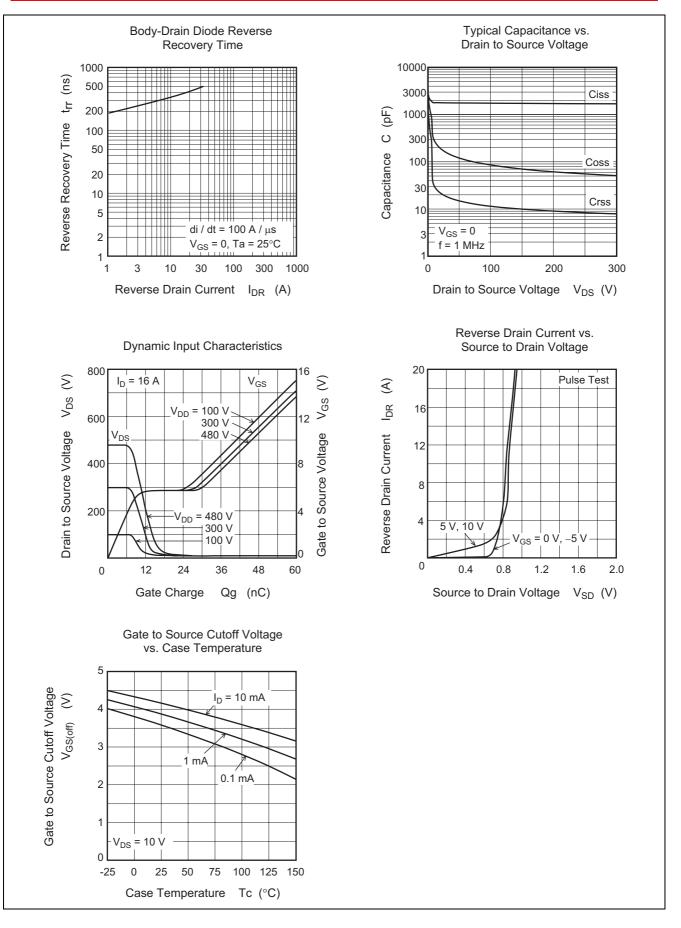
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Main Characteristics



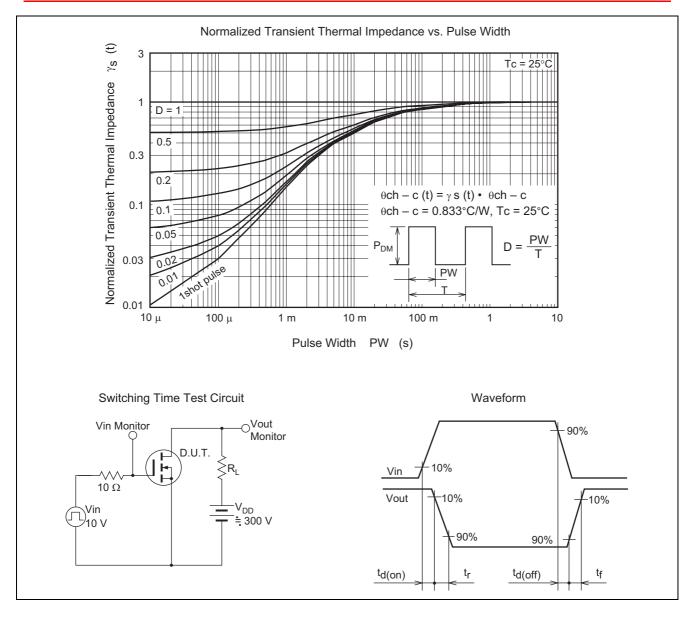
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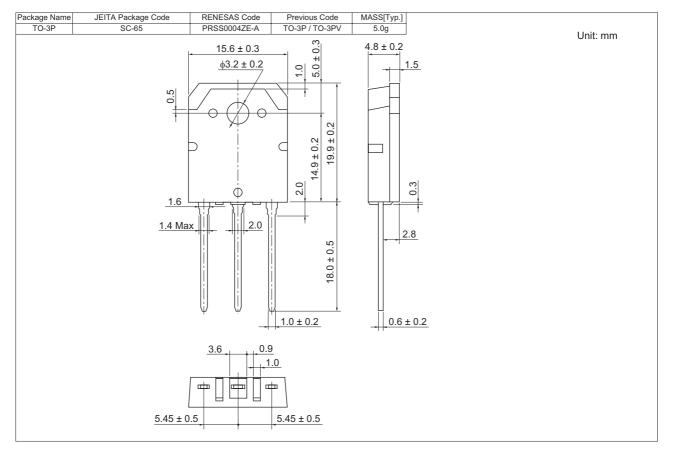


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Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK6014DPK-00-T0	360 pcs	Box (Tube)

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